

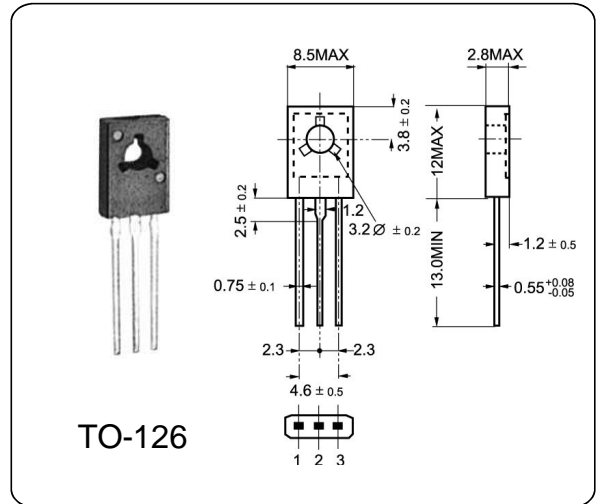


### DESCRIPTION

It is intended for use in power amplifier and switching applications.

### ABSOLUTE MAXIMUM RATINGS ( Ta = 25 °C)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	40	V
Collector-Emitter Voltage	$V_{CEO}$	30	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	3.0	A
Base Current	$I_B$	0.3	A
Total Dissipation at	$P_{tot}$	10	W
Max. Operating Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{stg}$	-55~150	°C



### ELECTRICAL CHARACTERISTICS ( Ta = 25 °C)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector Cut-off Current	$I_{CEO}$	$V_{CB}=30V, I_E=0$			0.01	mA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB}=3V, I_C=0$			0.01	mA
Collector-Emitter Sustaining Voltage	$V_{CEO}$	$I_C=10mA, I_B=0$	30			V
DC Current Gain	$h_{FE(1)}$	$V_{CE}=2V, I_C=20mA$	30	150		
	$h_{FE(2)}$	$V_{CE}=2V, I_C=1.0A$	60	160	400	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=2A, I_B=200mA$		0.3	0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=2A, I_B=200mA$		1.0	2.0	V
Current Gain Bandwidth Product	$f_T$	$V_{CE}=5V, I_C=100mA$		90		MHz